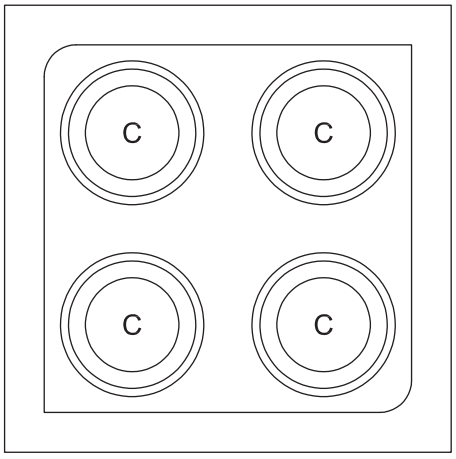
PROCESS CPZ39R
Transient Voltage Suppressor
5 Volt Quad TVS Chip

PROCESS DETAILS

Die Size	11 x 11 MILS
Die Thickness	3.94 MILS
Cathode Bonding Pad Areas (4)	3.54 MILS DIAMETER EACH
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 9,000Å

GEOMETRY



BACKSIDE ANODE R0

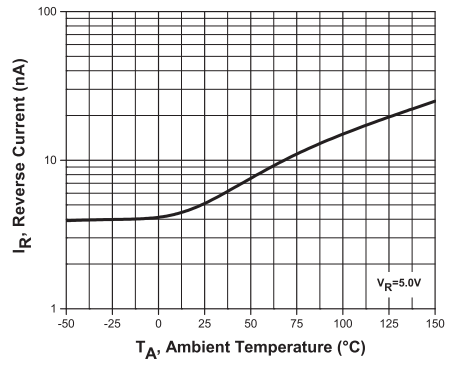
GROSS DIE PER 5 INCH WAFER
140,490

PRINCIPAL DEVICE TYPE
CMNTVS5V0

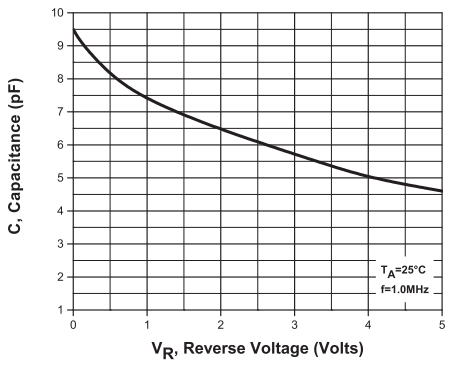
PROCESS CPZ39R

Typical Electrical Characteristics

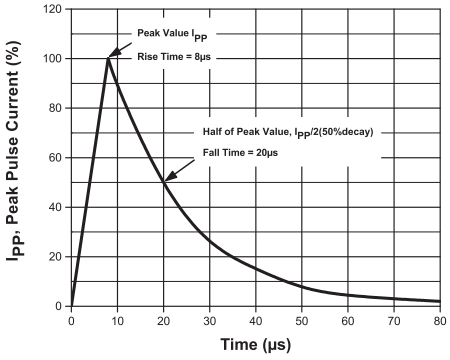
Leakage Current



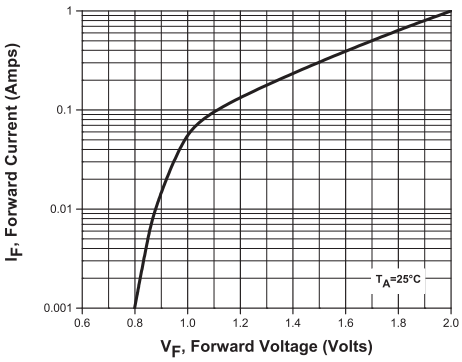
Capacitance



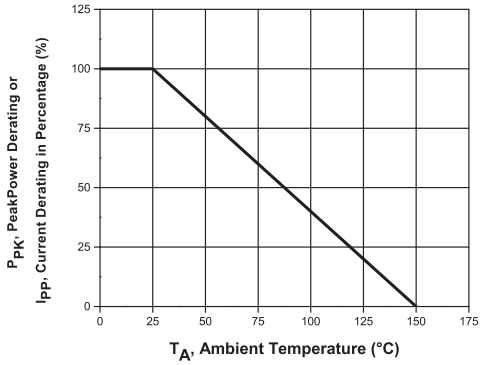
8 x 20 µs Pulse Waveform



Forward Voltage



Normalized Power & Current Derating



R0 (22-January 2013)